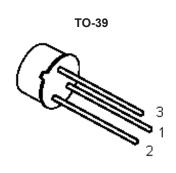
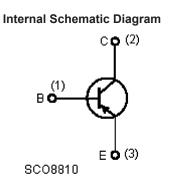
Transistor









Description:

The 2N5680 are high voltage silicon epitaxial planar PNP transistors in JEDEC TO-39 metal case intended for use as drivers for high power transistors in general purpose, amplifier and switching circuit.

Feature:

· NPN transistors

Applications

- · General Purpose Switching
- · General Purpose Amplifiers

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-Base Voltage (I _E = 0)	V _{CBO}	-120		
Collector-Emitter Voltage (I _B = 0)	V _{CEO}	-120	V	
Emitter-Base Voltage (I _C = 0)	V _{EBO}	-4		
Collector Current	I _C -1		_	
Base Current	I _B	-0.5	A	
Total Dissipation at T _C ≤25°C		10	W	
Total Dissipation at T _a ≤50°C	P _{tot}	1	VV	
Storage Temperature	T _{stg}	-65 to 200	°C	
Maximum Operating Junction Temperature	T _j	200	C	

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro



Transistor



Thermal Data

Parameter	Symbol	Value	Unit	
Maximum Thermal Resistance Junction-case	R _{thj-case}	17.5	°C/W	
Maximum Thermal Resistance Junction-ambient	R _{thi-a}	175		

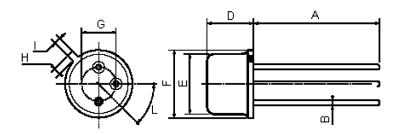
Electrical Characteristics ($T_C = 25^{\circ}C$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector Cut-off Current (V _{BE} = -1.5V)	2N5680 V _{CE} = -120V T _C = 150°C 2N5680 V _{CE} = -120V	I _{CEV}	-	-	-1 -1	
Collector Cut-off Current (I _E = 0)	2N5680 V _{CB} = -120V	I _{CBO}	1	1	-1	μA
Collector Cut-off Current (I _B = 0)	2N5680 V _{CB} = -80V	I _{CEO}			-10	P 1
Emitter Cut-off Current (I _C = 0)	V _{EB} = -4V	I _{EBO}	-	-	-1	
Collector-Emitter Sustaining Voltage	2N5680 I _C = -10mA	V _{CEO}	-120	-	-	
Collector-Emitter Saturation Voltage	$I_{C} = -250 \text{mA}$ $I_{B} = -25 \text{mA}$ $I_{C} = -500 \text{mA}$ $I_{B} = -50 \text{mA}$ $I_{C} = -1 \text{mA}$ $I_{B} = -200 \text{mA}$	V _{CE (sat)} *	1	1	-0.6 -1 -2	V
Base-Emitter Voltage	$I_{\rm C} = -250 {\rm mA}$ $V_{\rm CE} = -2 {\rm V}$	V _{BE} *	-	-	-1	
DC Current Gain	$I_{C} = -250 \text{mA}$ $V_{CE} = -2V$ $I_{C} = -1 \text{A}$ $V_{CE} = -2 \text{V}$	h _{FE} *	40 5	-	150	-
Small Signal Current Gain	$I_{C} = -0.2A$ $V_{CE} = -1.5V$ $f = 1kHz$	h _{fe}	40	-	-	-
Transition frequency	I _C = -100mA V _{CE} = -10V f = 10MHz	f _T	30	-	-	MHz
Collector Base Capacitance	I _E = 0 V _{CB} = -20V f = 1MHz	C _{CBO}	-	-	50	pF

^{*}Pulsed: Pulse Duration = 300ms, Duty Cycle 1.5%.

Transistor





TO-39 Mechanical Data

Dimension	mm		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	12.7	-	-	0.5	-	
В	-	-	0.49	-	-	0.019
D	-	-	6.6	-	-	0.26
E	-	-	8.5	-	-	0.334
F	-	-	9.4	-	-	0.37
G	5.08	-	-	0.2	-	-
Н	-	-	1.2	-	-	0.047
I	-	-	0.9	-	-	0.035
L	45° (Typical)					

Part Number Table

Description	Part Number		
Transistor	2N5680		

Important Notice: This data sheet and its contents (the "Information") belong to the members of the AVNET group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp Pro is the registered trademark of Premier Farnell Limited 2019.

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro

